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電源管理



顯示驅動



二三極管



LDO穩壓器



觸摸芯片



MOS管



運算放大器



存儲芯片



MCU



串口通信

BCX56

產品規格說明書

BCX56 NPN Plastic-Encapsulate Transistors

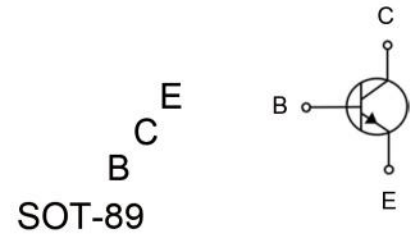
Features

- Collector Current: $I_C = 1A$
- Power Dissipation of 500mw

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
BCX54,BCX55 ,BCX56	SOT-89	BCX5x	1000

x:From 4,4-10,4-16
5,5-10,5-16
6,6-10,6-16



Maxmim Ratings (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	BCX54 45	V
		BCX55 8	
		BCX56 100	
V_{CEO}	Collector-Emitter Voltage	BCX54 45	V
		BCX55 8	V
		BCX56 8	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	1	A
P_C	Collector Power Dissipation	500	mW
T_j	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-55-150	°C

BCX56 NPN Plastic-Encapsulate Transistors

Electrical Characteristics (Ta=25°C unless otherwise specified)

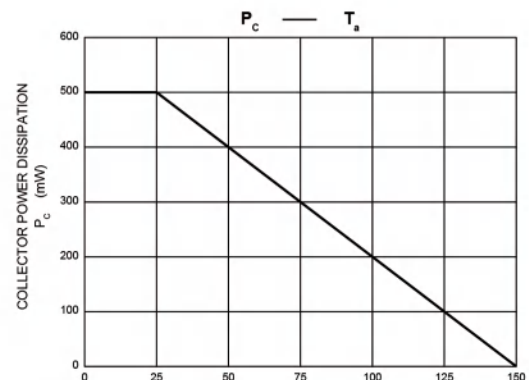
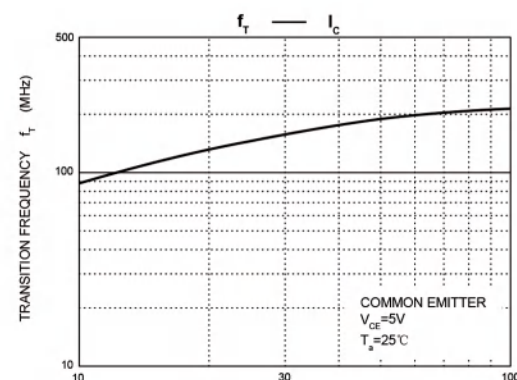
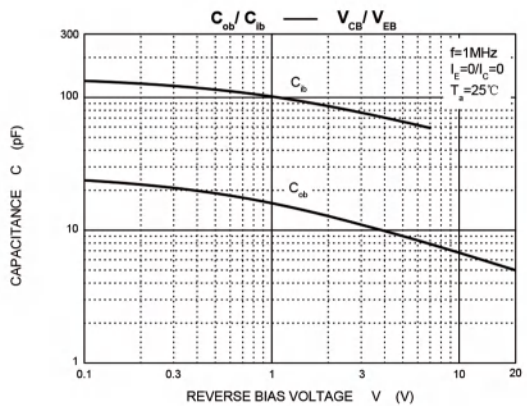
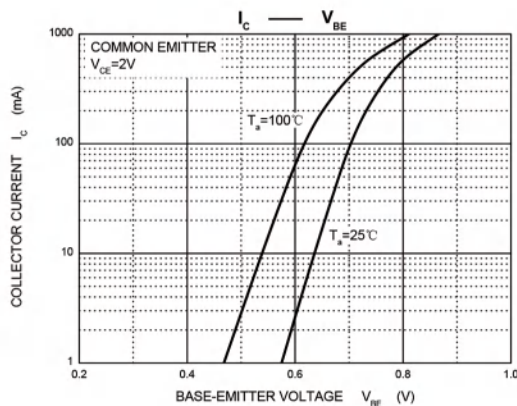
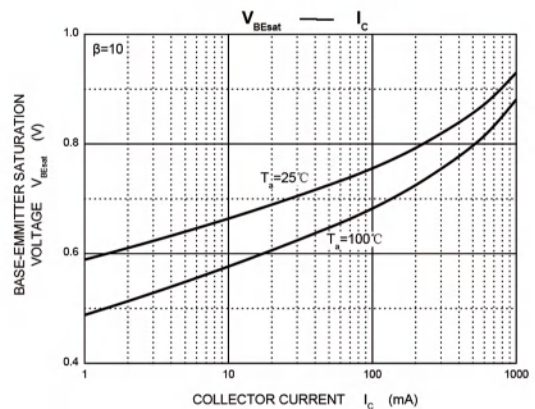
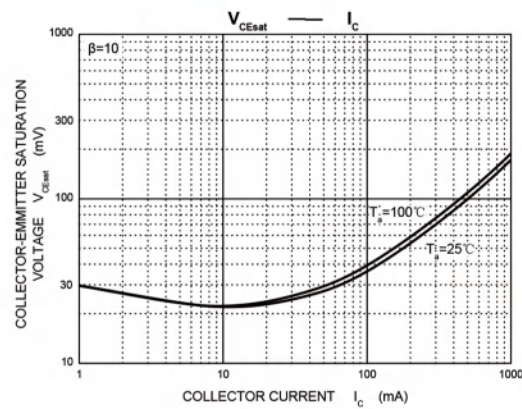
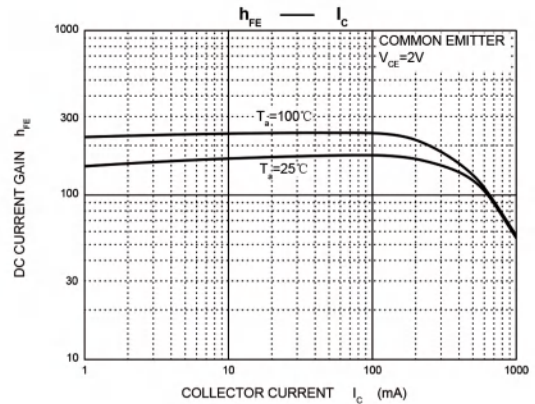
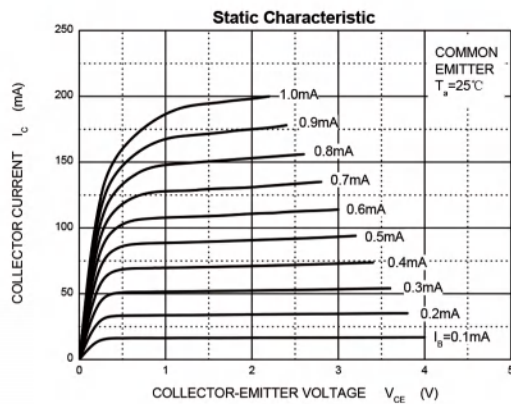
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	BCX54	45		V
			BCX55	60		
			BCX56	100		
Collector-emitter breakdown voltage	$V_{(BR)CEO}^*$	$I_C=10mA, I_B=0$	BCX54	45		V
			BCX55	60		
			BCX56	80		
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$		5		V
Collector cut-off current	I_{CBO}	$V_{CB}=30V, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5V, I_C=0$			0.1	μA
DC current gain	$h_{FE(1)}^*$	$V_{CE}=2V, I_C=5mA$	40			
	$h_{FE(2)}^*$	$V_{CE}=2V, I_C=150mA$	63		250	
	$h_{FE(3)}^*$	$V_{CE}=2V, I_C=0.5A$	25			
Collector-emitter saturation voltage	$V_{CE(sat)}^*$	$I_C=0.5A, I_B=50mA$			0.5	V
Base-emitter voltage	V_{BE}^*	$V_{CE}=2V, I_C=0.5A$			1	V
Transition frequency	f_T	$V_{CE}=5V, I_C=10mA, f=100MHz$		130		MHz

Classification Of h_{FE}

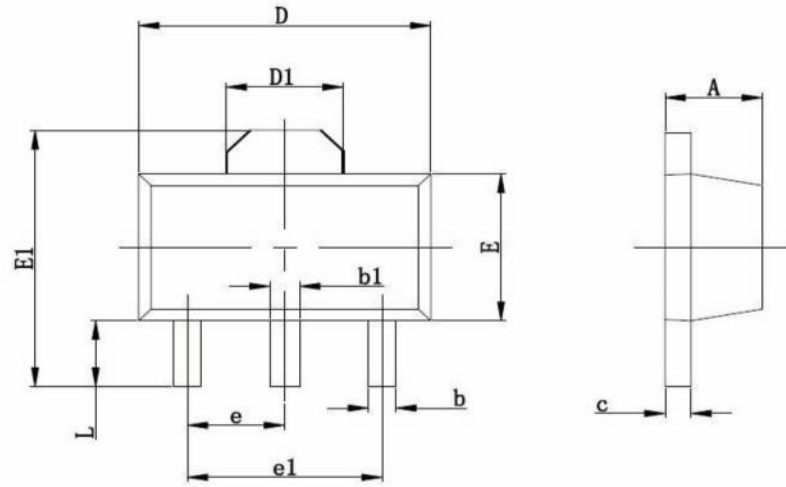
Rank	BCX54,BCX55 BCX56	BCX54-10,BCX55-10 BCX56-10	BCX54-16,BCX55-16 BCX56-16
Range	63-250	63-160	100-250

BCX56 NPN Plastic-Encapsulate Transistors

Typical Characteristics



BCX56 NPN Plastic-Encapsulate Transistors SOT-89 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.400	1.600	0.055	0.063
b	0.320	0.520	0.013	0.020
b1	0.400	0.580	0.016	0.023
c	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550 REF.		0.061 REF.	
E	2.300	2.600	0.091	0.102
E1	3.940	4.250	0.155	0.167
e	1.500 TYP.		0.060 TYP.	
e1	3.000 TYP.		0.118 TYP.	
L	0.900	1.200	0.035	0.047